



30V P-Channel Trench Power MOSFET

General Description

The SJM30P095 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

Features

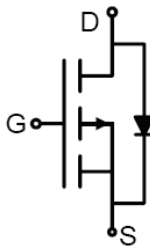
- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired

Application

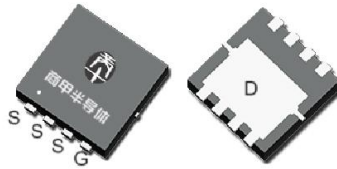
- PWM Applications
- Load Switch
- Power Management

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	-30	V
$R_{DS(ON_TYP)}$	10.6	m Ω
I_D	-40	A
Q_G	38	nC



Schematic Diagram



PDFN3X3-8L top&bottom view



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJM30P095	SJM30P095	PDFN3X3-8L	Tape	\	\	5000 Pcs

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	-30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_c=25^\circ\text{C}$)	-40	A
	Drain Current-Continuous($T_c=100^\circ\text{C}$)	-25	A
I_{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-160	A
P_D	Maximum Power Dissipation($T_c=25^\circ\text{C}$)	34	W
	Maximum Power Dissipation($T_c=100^\circ\text{C}$)	14	W
E_{AS}	Avalanche energy (Note 2)	100	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to- Case		3.7	$^\circ\text{C/W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =25℃			-1	μA
		V _{DS} =-30V, V _{GS} =0V T _J =125℃			-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.2		-2	V
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-6A		14		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-6A T _J =25℃		10.6	13.3	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-4A T _J =25℃		14.8	19.7	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V,V _{GS} =0V, f=1.0MHz		1470		pF
C _{oss}	Output Capacitance			165		pF
C _{rss}	Reverse Transfer Capacitance			131		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		13		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =-10V, V _{DS} =-15V, R _L =2.5Ω, R _{GEN} =3Ω		14.6		nS
t _r	Turn-on Rise Time			3		nS
t _{d(off)}	Turn-Off Delay Time			91.2		nS
t _f	Turn-Off Fall Time			35.6		nS
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-6A		38		nC
Q _{gs}	Gate-Source Charge			8		nC
Q _{gd}	Gate-Drain Charge			9		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				-40	A
V _{SD}	Forward on Voltage ^(Note 3)	V _{GS} =0V, I _S =-6A			-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-6A, dI/dt=-100A/μs		14.2		ns
Q _{rr}	Reverse Recovery Charge	I _F =-6A, dI/dt=-100A/μs		5		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

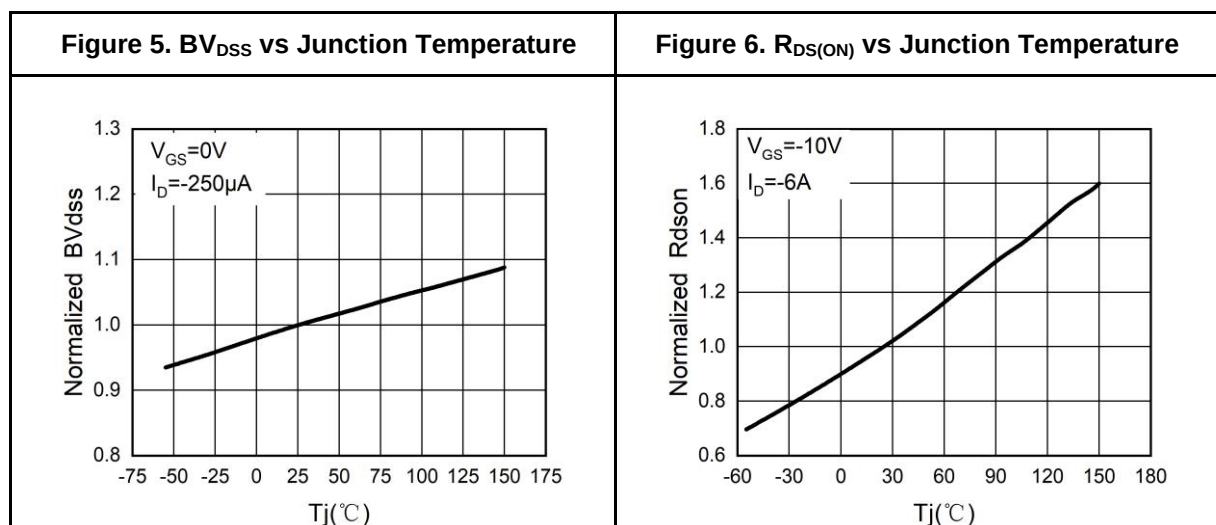
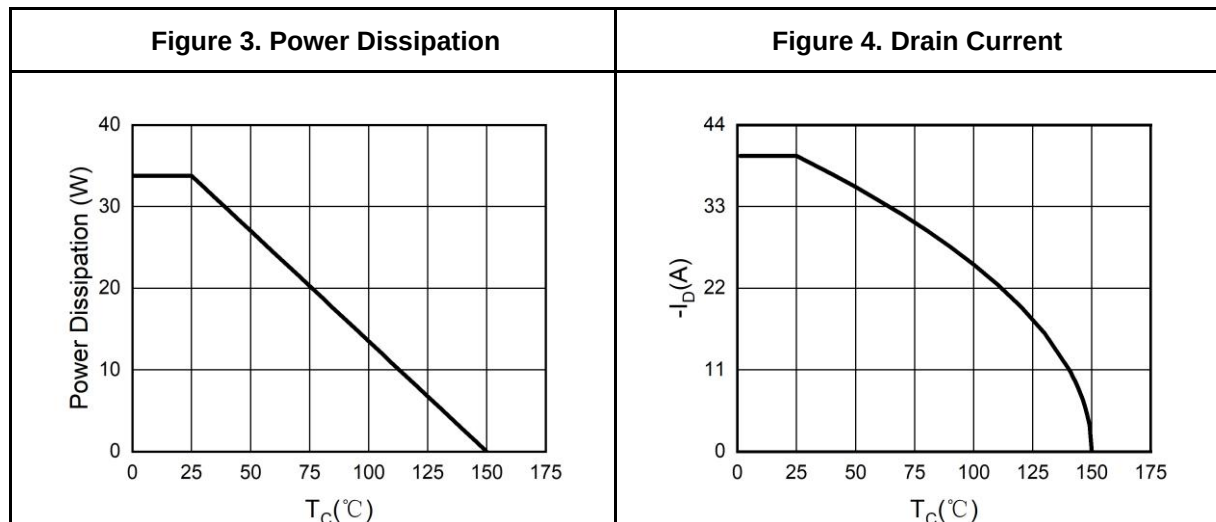
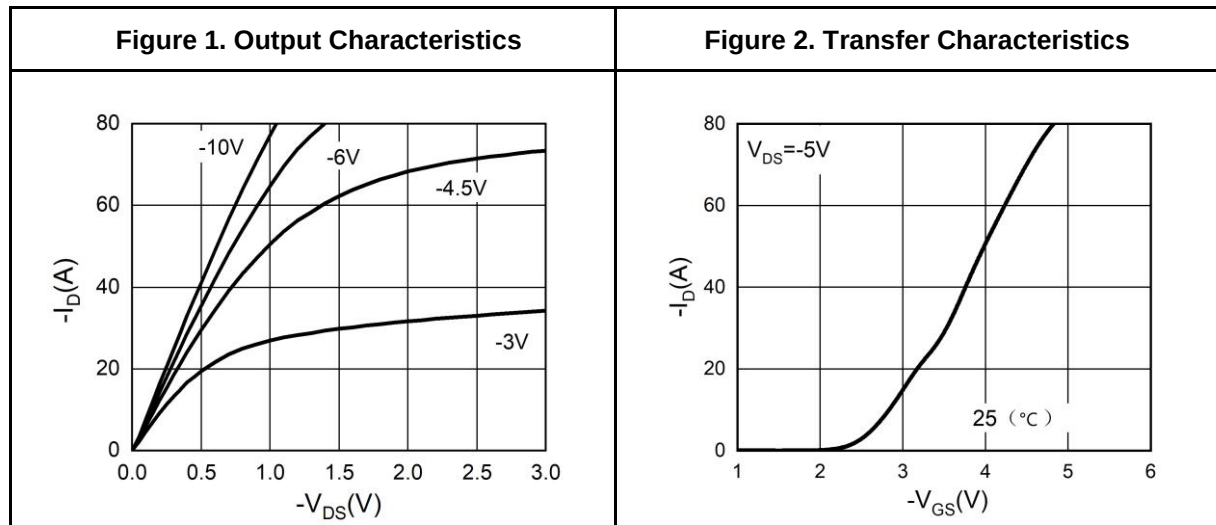
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=-25V, V_G=-10V, R_g=25\Omega, L=0.5\text{mH}$.

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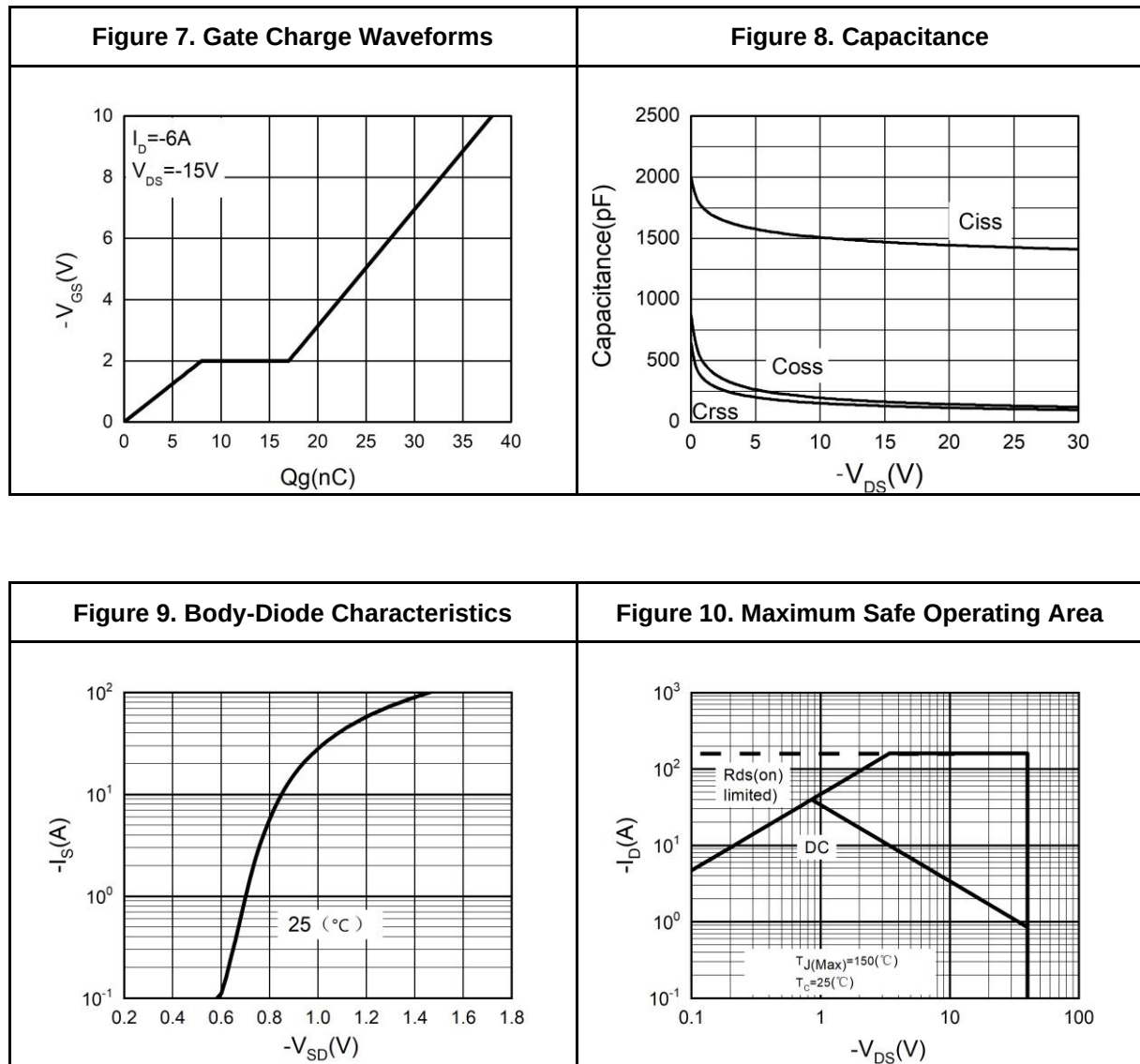
Typical Electrical And Thermal Characteristics (Curves)





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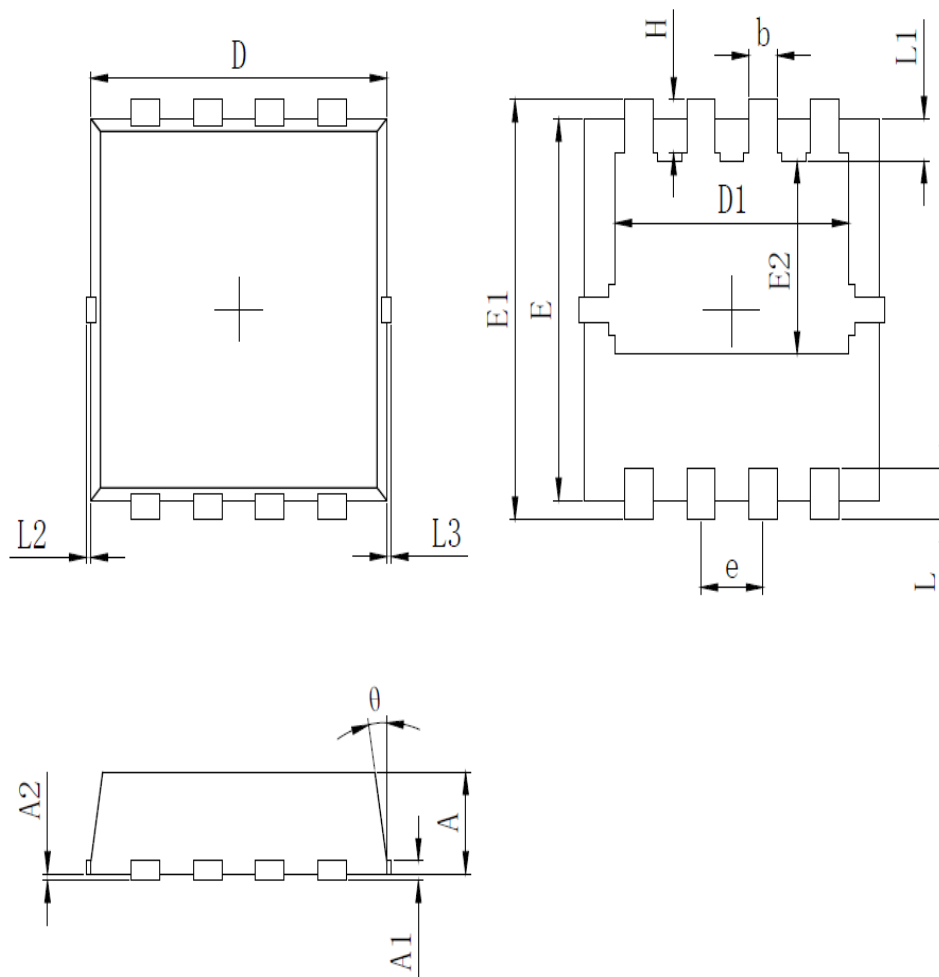
Typical Electrical And Thermal Characteristics (Curves)





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PDFN3X3-8L Package Information



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.700	0.800	0.900
A1	0.152 REF.		
A2	0°0.05		
D	3.000	3.100	3.200
D1	2.300	2.450	2.600
E	2.900	3.000	3.100
E1	3.150	3.300	3.450
E2	1.320	1.520	1.720
b	0.200	0.300	0.400
e	0.550	0.650	0.750
L	0.300	0.400	0.500
L1	0.180	0.330	0.480
L2	0°0.100		
L3	0°0.100		
H	0.315	0.415	0.515
θ	8°	10°	12°



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Attention

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